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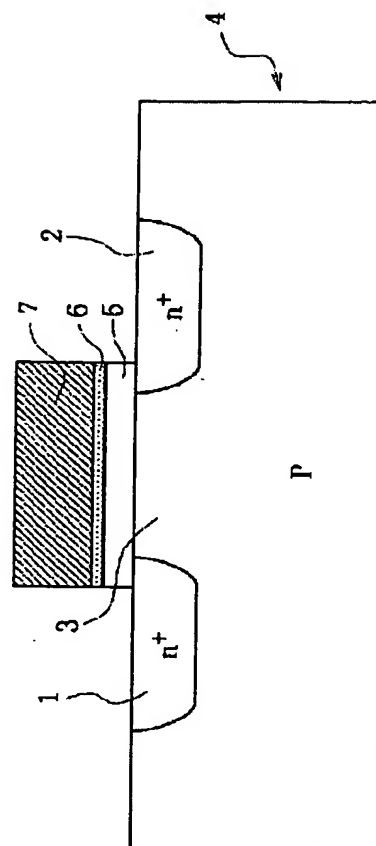
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TITLE : MOS DEVICE AND ITS
MANUFACTURING METHOD



ABSTRACT : PROBLEM TO BE SOLVED: To prevent the mutual conductance and current drive capacity of a MOS transistor from decreasing.

SOLUTION: A carbon compound layer 6 that is disposed between a gate oxide film 5 and a polycrystalline silicon gate electrode 7 prevents an impurity in the polycrystalline silicon gate electrode 7 from proceeding to the gate oxide film 5. As a result, by thinning the gate oxide film 5, gate capacity cannot be decreased remarkably, thus preventing mutual conductance and current drive capacity from decreasing.

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